

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Counts
1	BRS	L1	5311	((gate near5 source)near5 capacit\$4)	USPA T	2001/10/2 4 12:26			0
2	BRS	L2	3481	(power adj2 mosfet)	USPA T	2001/10/2 4 13:11			0
3	BRS	L3	29382	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	USPA T	2001/10/2 4 13:11			0
4	BRS	L4	112	diffusion near3 (source and channel)	USPA T	2001/10/2 4 13:12			0
5	BRS	L5	9144	gate same (trench or groov\$3)	USPA T	2001/10/2 4 13:22			0
6	BRS	L6	0	1 and 2 and 3 and 4 and 5	USPA T	2001/10/2 4 11:41			0
7	BRS	L7	1	1 and 2 and 3 and 5	USPA T	2001/10/2 4 11:42			0
8	BRS	L8	46	2 and 3 and 5	USPA T	2001/10/2 4 11:42			0
9	BRS	L9	115	((gate near5 source)near5 capacit\$4)	US-P GPUB	2001/10/2 4 12:39			0
10	BRS	L10	74	(power adj2 mosfet)	US-P GPUB	2001/10/2 4 12:39			0
11	BRS	L11	545	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	US-P GPUB	2001/10/2 4 12:39			0
12	BRS	L13	342	gate same (trench or groov\$3)	US-P GPUB	2001/10/2 4 12:39			0
13	BRS	L12	4	diffusion near3 (source and channel)	US-P GPUB	2001/10/2 4 12:39			0
14	BRS	L14	0	9 and 10 and 11 and 13	US-P GPUB	2001/10/2 4 12:28			0
15	BRS	L15	0	9 and 11 and 13	US-P GPUB	2001/10/2 4 12:29			0
16	BRS	L17	13	11 and 13 and MOSFET	US-P GPUB	2001/10/2 4 12:29			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
17	BRS	L16	58	11 and 13	US-P GPUB	2001/10/2 4 12:33			0
18	BRS	L18	280	((gate near5 source)near5 capacit\$4)	EPO	2001/10/2 4 12:47			0
19	BRS	L19	406	(power adj2 mosfet)	EPO	2001/10/2 4 12:47			0
20	BRS	L20	1420	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	EPO	2001/10/2 4 12:47			0
21	BRS	L21	1247	gate same (trench or groov\$3)	EPO	2001/10/2 4 12:48			0
22	BRS	L22	2	diffusion near3 (source and channel)	EPO	2001/10/2 4 12:48			0
23	BRS	L23	0	18 and 19 and 20 and 21	EPO	2001/10/2 4 12:42			0
24	BRS	L24	0	18 and 19 and 20	EPO	2001/10/2 4 12:41			0
25	BRS	L25	5	19 and 20	EPO	2001/10/2 4 12:41			0
26	BRS	L26	6	18 and 19	EPO	2001/10/2 4 12:41			0
27	BRS	L27	16	20 and 21	EPO	2001/10/2 4 12:42			0
28	BRS	L28	1009	((gate near5 source)near5 capacit\$4)	JPO	2001/10/2 4 13:04			0
29	BRS	L29	4122	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	JPO	2001/10/2 4 12:47			0
30	BRS	L30	635	(power adj2 mosfet)	JPO	2001/10/2 4 12:47			0
31	BRS	L31	4398	gate same (trench or groov\$3)	JPO	2001/10/2 4 13:03			0
32	BRS	L33	0	28 and 29 and 30 and 31 and 32	JPO	2001/10/2 4 12:51			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Rows
33	BRS	L32	11	diffusion near3 (source and channel)	JPO	2001/10/2 4 12:49			0
34	BRS	L34	0	29 and 32	JPO	2001/10/2 4 12:50			0
35	BRS	L35	4122	29 and poly	JPO	2001/10/2 4 12:50			0
36	BRS	L36	0	28 and 29 and 30 and 31	JPO	2001/10/2 4 13:04			0
37	BRS	L37	0	29 and 30 and 31	JPO	2001/10/2 4 12:52			0
38	BRS	L38	84	29 and 31	JPO	2001/10/2 4 12:52			0
39	BRS	L39	84	29 and 31 and poly	JPO	2001/10/2 4 12:52			0
40	BRS	L40	3403	gate same (poly and trench or groov\$3)	JPO	2001/10/2 4 13:03			0
41	BRS	L41	1031	((gate near5 source)near5 capacit\$4)	DERW ENT	2001/10/2 4 13:04			0
42	BRS	L42	10	28 and 29	JPO	2001/10/2 4 13:04			0
43	BRS	L43	1448	(power adj2 mosfet)	DERW ENT	2001/10/2 4 13:11			0
44	BRS	L44	15407	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	DERW ENT	2001/10/2 4 13:12			0
45	BRS	L45	13	diffusion near3 (source and channel)	DERW ENT	2001/10/2 4 13:12			0
46	BRS	L46	4093	gate same (trench or groov\$3)	DERW ENT	2001/10/2 4 13:22			0
52	BRS	L52	1	43 and 44 and 46	DERW ENT	2001/10/2 4 13:26			0
53	BRS	L53	161	44 and 46	DERW ENT	2001/10/2 4 13:26			0
54	BRS	L54	31	44 and 46 and diffusion	DERW ENT	2001/10/2 4 13:26			0